

Silicon Carbide Schottky Rectifiers

PRODUCT PREVIEW

DESCRIPTION

In Microsemi's new Powermite® SMT package, these high efficiency ultrafast rectifiers offer the power handing capabilities previously found only in much larger packages. They are ideal for SMD applications that operate at high frequencies.

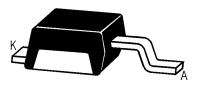
In addition to its size advantages, Powermite® package features include a full metallic bottom that eliminates the possibility of solder flux entrapment during assembly, and a unique locking tab acts as an integral heat sink. Its innovative design makes this device ideal for use with automatic insertion equipment.

IMPORTANT: For the most current data, consult *MICROSEMI*'s website: http://www.microsemi.com

ABSOLUTE MAXIMUM RATINGS AT 25° C (UNLESS OTHERWISE SPECIFIED) Rating Symbol Value Unit ٧ Maximum Reverse Voltage, UPSC100 100 Vdc ٧ Maximum Reverse Voltage, UPSC200 200 Vdc Maximum Average Output Current, Т 1.0 Adc T_{TAB} =75°C Non-Repetitive Sinusoidal Surge Current Ι 15 Α (8.3 mS) ٥С Storage Temperature -55 to +150 T stg ٥С -55 to +150 Operating Temperature T op

CTERISTICS	5	
E SPECIFIE	D)	
<u> </u>		
Rjtab	30	°C/Watt
Rja (1)	10	°C/Watt
	Rjtab	1

(1) When Mounted on PC board with 2 ounce copper pattern.



KEY FEATURES

- High power surface mount package.
- Silicon carbide Schottky rectifiers no reverse voltage recovery.
- Internal heat sink locking tabs
- Low forward voltage.
- Full metallic bottom eliminates flux entrapment
- Compatible with automatic insertion equipment
- Low profile-maximum height of 1mm supplied in 8mm tape and reel- 3,000 units/ 7" reel; 12,000 units/ 12" reel

APPLICATIONS/BENEFITS

- Switching and Regulating Power Supplies.
- Charge Pump Circuits.
- Reduces reverse recovery loss due to low IRM.
- Small foot print

.100 X .105 mils
1:1 Actual size





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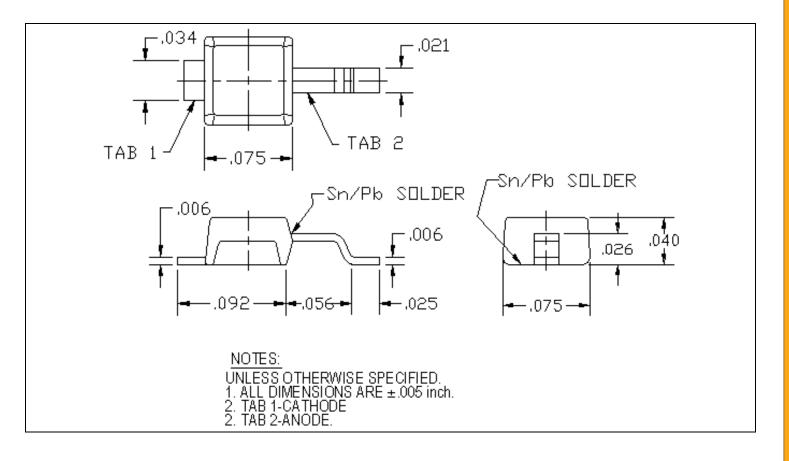
ELE	ELECTRICAL PARAMETERS @ 25°C (unless otherwise specified)					
Parameter	Symbol	Conditions	Min	Тур.	Max	Units
► Off Characteristics						
Forward Voltage:	V _F	I _F = 1 A			2.0	V
Reverse Current:	I_{R}	V _R = Max Rating			100	μΑ
▶ Dynamic characteristics				-		
Capacitance	Ст	$V_R = 5V; F = 1 MH_Z$			80	pF

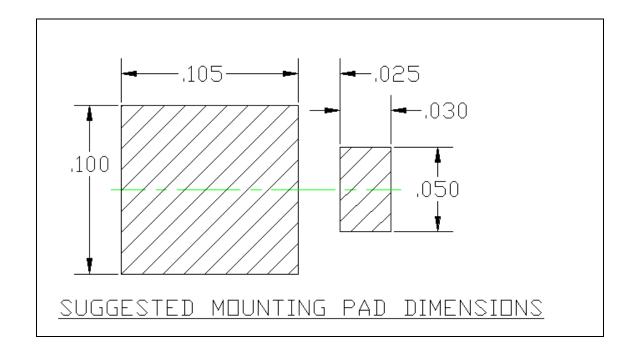
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